

60V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
60V	$19m\Omega @ V_{GS} = 10V$	33.2A		
	28mΩ @ V _{GS} = 4.5V	28A		

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production –
 Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

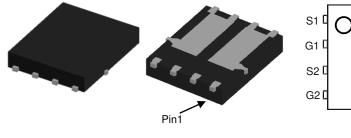
Description and Applications

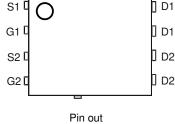
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

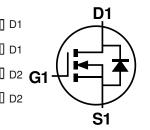
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

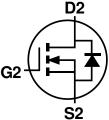
Mechanical Data

- Case: PowerDI[®]5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)









Top View Bottom View Top View

Equivalent Circuit

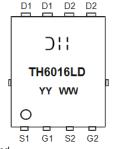
Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH6016LPDQ-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking TH6016LD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 7)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	Ι _D	33.2 23.7	А
Continuous Drain Current (Note 6) $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		ID	9.2 6.5	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	50	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	31	Α	
Pulsed Body Diode Forward Current (Note 6)	I _{SM}	50	Α	
Avalanche Current, L = 0.1mH	I _{AS}	15.3	Α	
Avalanche Energy, L = 0.1mH	Eas	11.7	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\Theta JA}$	58	°C/W
Total Power Dissipation (Note 7)	P_D	37.5	W
Thermal Resistance, Junction to Case (Note 7)	R _{OJC}	4	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +175	°C

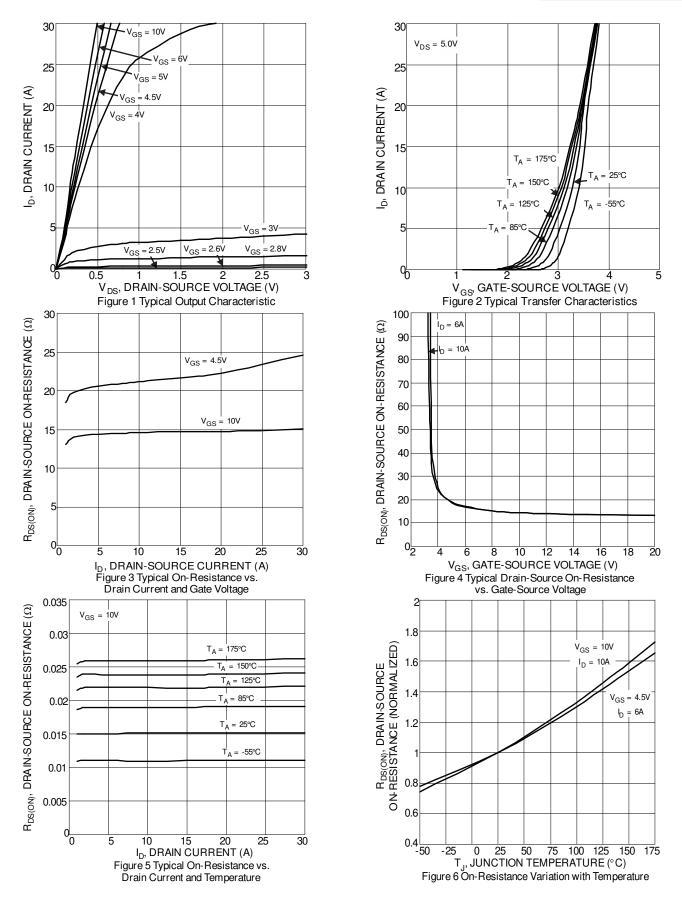
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	14.5	19	mΩ	V _{GS} = 10V, I _D = 10A	
Static Drain-Source On-Nesistance		_	20.9	28		V _{GS} = 4.5V, I _D = 6A	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	V _{GS} = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{ISS}	_	864	_	pF		
Output Capacitance	Coss	_	282	_	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{RSS}	_	27	_	pF	11 = 11VII 12	
Gate Resistance	Rg	_	1.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q _G	_	8.4	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q _G	_	17	_	nC	, , , , , , , , , , , , , , , , , , ,	
Gate-Source Charge	Q _{GS}	_	3.1	_	nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	Q _{GD}	_	4.3	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns		
Turn-On Rise Time	t _R	_	5.2	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 10A, R_{G} = 6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	13	_	ns		
Turn-Off Fall Time	t _F	_	7	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	22	_	ns	1 400 11/14 4000/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	11	_	nC	$I_F = 10A$, di/dt = $100A/\mu$ s	

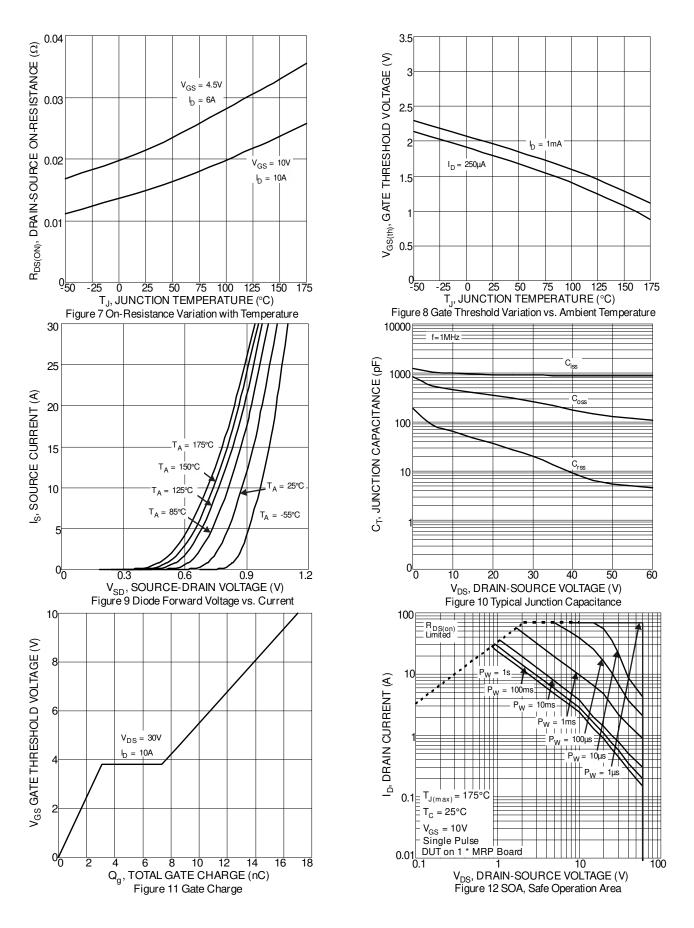
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).8. Short duration pulse test used to minimize self-heating effect. Notes:

^{9.} Guaranteed by design. Not subject to product testing.

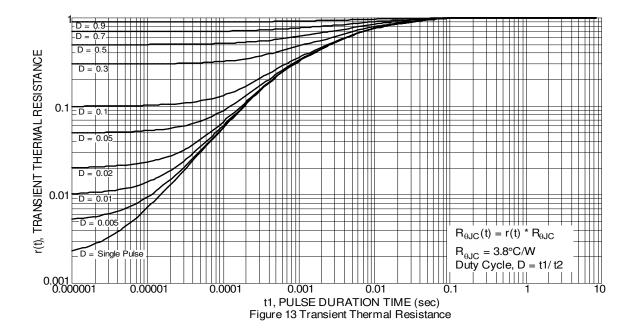










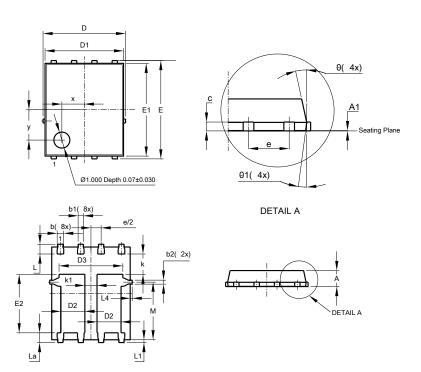




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)

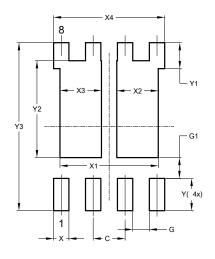


PowerDI5060-8 (Type C)					
Dim	Min				
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	ļ	5.15 BSC			
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	-	-	3.98		
Е	•	3.15 BSC)		
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1.27BSC				
k	-	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
M	3.50	3.71	3.605		
X	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value		
Dimensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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